

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1.3	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3k	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	-	MAX.	15	mA
		-		25	
I _H	I _T =100mA		MAX.	15	mA
dV/dt	V _D =540V Gate Open T _j =110		MIN.	100	V s
(dV/dt)c	(dI/dt)c=1.8A/ms, T _j =110		MIN.	2.5	9 V
t _{on}	I _G =20mA I _A =200mA I _R =20mA T _j =25		TYP.	1	s
t _{off}				12	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5A$ $t_p=380$ s	$T_j=25$	1.7	V
V_{TO}	Threshold voltage	$T_j=125$	0.94	V
R_D	Dynamic resistance	$T_j=125$	124	P
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	15	/W
$R_{th(j-a)}$	junction to ambient (AC)	150	/W

ORDERING INFORMATION

J ST 136 W -800 D

JieJie Microelectronics Co., Ltd.

Triacs

800:V

FIG.1: Maximum power dissipation versus RMS
on-state current

FIG.2: RMS on-state current versus case
temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

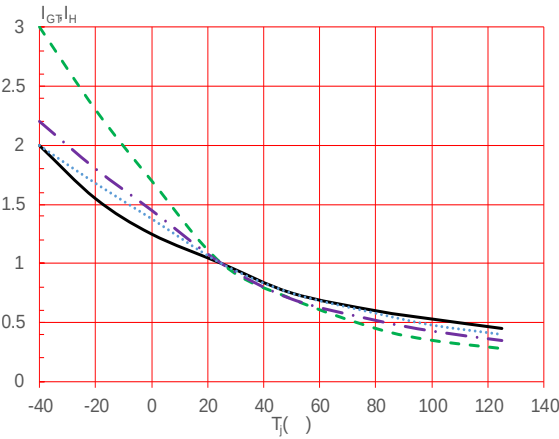
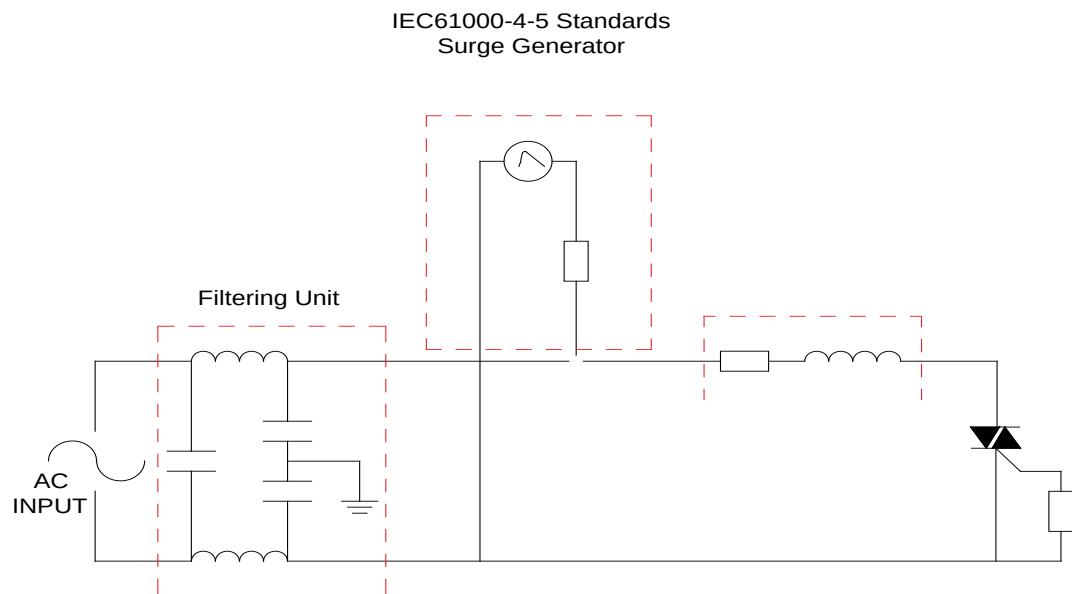


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



	IGT(mA)		Package	Base qty. (pcs)	

PACKAGE MECHANICAL DATA

